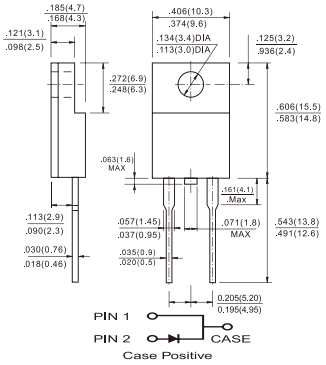
TAIWAN SEMICONDUCTOR

MBRF5100 - MBRF5200

Isolated 5.0 AMPS. Schottky Barrier Rectifiers

ITO-220AC

RoHS COMPLIANCE



Dimensions in inches and (millimeters)

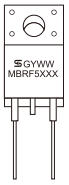
Features

- ✧ Plastic material used carries Underwriters Laboratory Classifications 94V-0
- ✧ Metal silicon rectifier, majority carrier conduction
- ✧ Low power loss, high efficiency
- ✧ High current capability, low forward voltage drop
- ✧ High surge capability
- ✧ For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- ✧ Guardring for overvoltage protection
- ✧ High temperature soldering guaranteed: 260°C/10 seconds,0.25"(6.35mm)from case
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode

Mechanical Data

- ✧ Cases: JEDEC ITO-220AC molded plastic body
- ✧ Terminals: Lead solderable per MIL-STD-750, Method 2026
- ✧ Polarity: As marked
- ✧ Mounting position: Any
- ✧ Mounting torque: 5 in. - lbs. max
- ✧ Weight: 1.61 grams

Marking Diagram



MBRF5XXX = Specific Device Code
G = Green Compound
Y = Year
WW = Work Week

Maximum Ratings and Electrical Characteristics

Rating at 25°Cambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Type Number	Symbol	MBRF 5100	MBRF 5150	MBRF 5200	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	100	150	200	V
Maximum RMS Voltage	V_{RMS}	70	105	140	V
Maximum DC Blocking Voltage	V_{DC}	100	150	200	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	5			A
Peak Repetitive Forward Current (Square Wave, 20KHz) at Tc=105°C	I_{FRM}	10			A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	120			A
Peak Repetitive Reverse Surge Current (Note 2)	I_{RRM}	0.5			A
Maximum Instantaneous Forward Voltage at I_F=5A,T_A=25°C I_F=5A,T_A=125 °C	V_F	0.90 0.80	1.02 0.92		V
Maximum Instantaneous Reverse Current @ T_A =25 °C at Rated DC Blocking Voltage (Note 1) @ T_A=125 °C	I_R	0.1 5.0			mA mA
Voltage Rate of Change (Rated V_R)	dV/dt	10,000			V/uS
Typical Junction capacitance	Cj	310			pF
Maximum Thermal Resistance, (Note 3)	$R_{\theta JC}$	3.0			°C /W
Operating Junction Temperature Range	T_J	-65 to +150			°C
Storage Temperature Range	TSTG	-65 to +175			°C

Notes: 1. Pulse Test: 300us Pulse Width, 1% Duty Cycle
2. 2.0us Pulse Width, f=1.0 KHz
3. Mounted on Heatsink Size of 2 in x 3 in x 0.25 in Al-Plate.

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RATINGS AND CHARACTERISTIC CURVES (MBRF5100 THRU MBRF5200)

FIG.1- FORWARD CURRENT DERATING CURVE

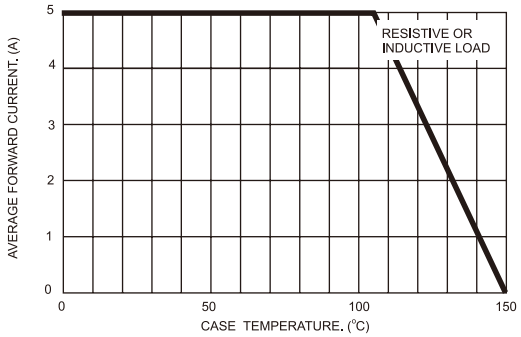

FIG.2- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

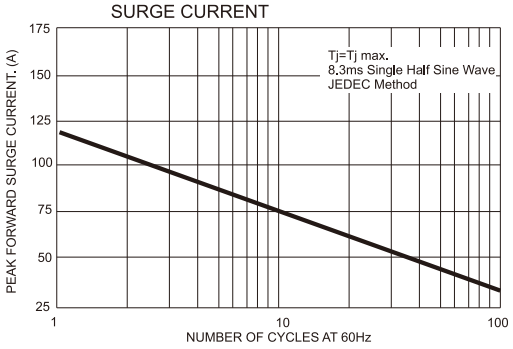

FIG.3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

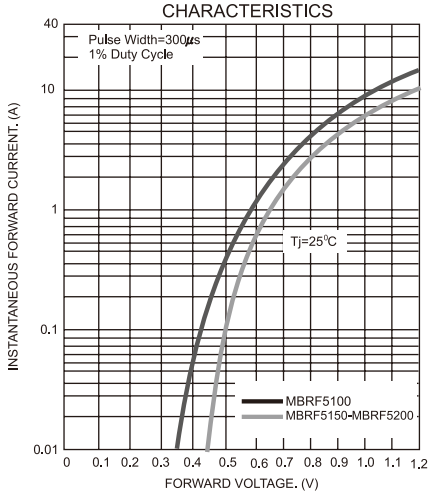

FIG.4- TYPICAL REVERSE CHARACTERISTICS

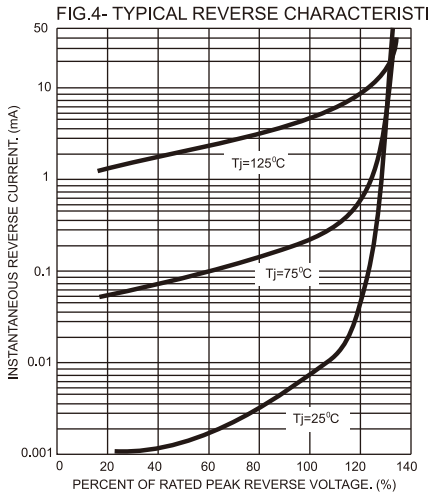

FIG.5- TYPICAL JUNCTION CAPACITANCE

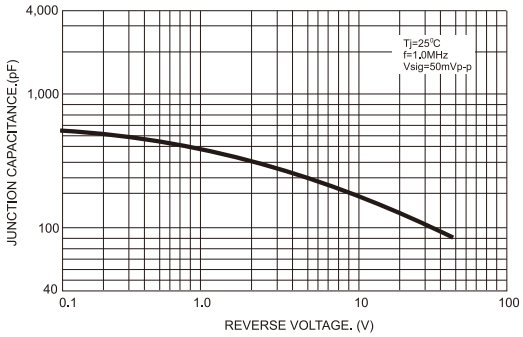

FIG.6- TYPICAL TRANSIENT THERMAL CHARACTERISTICS